OptiMOS™ - 6 Power-Transistor

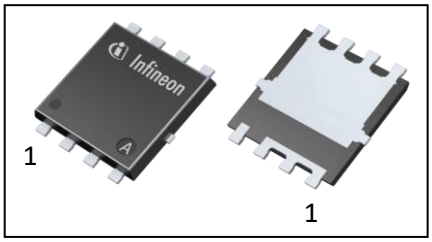
Product Summary

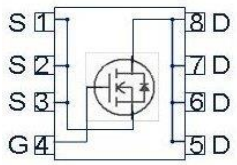
V_{DS}	40	V
$R_{DS(on),max}$	0.55	mΩ
I_D	120	A

Features

- OptiMOS™ - power MOSFET for automotive applications
- N-channel - Enhancement mode - Logic Level
- AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green Product (RoHS compliant)
- 100% Avalanche tested

PG-TDSON-8-53





Type	Package	Marking
IAUC120N04S6L005	PG-TDSON-8-53	6N04L005

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Drain current	I_D	V_{GS}=10V, Chip Limitation[1,2)]	435	A
		V_{GS}=10V, DC current[3)]	120	
		T_a=85°C, V_{GS}=10V, R_{thJA} on 2s2p[4,5)]	60	
Pulsed drain current[5)]	$I_{D,pulse}$	T_C=25°C, t_p=100µs	1550	
Avalanche energy, single pulse[2)]	E_{AS}	I_D=60A, R_G=25Ω	750	mJ
Avalanche current, single pulse	I_{AS}	R_G=25Ω	120	A
Gate source voltage	V_{GS}	-	±16	V
Power dissipation	P_{tot}	T_C=25°C	187	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	°C

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case[5)]	R_{thJC}	-	-	-	0.8	K/W
Thermal resistance, junction - ambient[4)]	R_{thJA}	-	-	26	-	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D= 1mA	40	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=130µA	1.2	1.6	2.0	
Zero gate voltage drain current	I_{DSS}	V_{DS}=40V, V_{GS}=0V, T_j=25°C	-	-	1	µA
		V_{DS}=40V, V_{GS}=0V, T_j=125°C[2)]	-	-	33	
Gate-source leakage current	I_{GSS}	V_{GS}=16V, V_{DS}=0V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=4.5V, I_D=60A	-	0.57	0.80	mΩ
		V_{GS}=10V, I_D=60A	-	0.43	0.55	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics[2]						
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz	-	8423	11203	pF
Output capacitance	C_{oss}		-	2294	2982	
Reverse transfer capacitance	C_{rss}		-	117	175	
Turn-on delay time	$t_{d(on)}$	V_{DD}=20V, V_{GS}=10V, I_D=120A, R_G=3.5Ω	-	9	-	ns
Rise time	t_r		-	8	-	
Turn-off delay time	$t_{d(off)}$		-	57	-	
Fall time	t_f		-	28	-	
Gate Charge Characteristics[2]						
Gate to source charge	Q_{gs}	V_{DD}=32V, I_D=120A, V_{GS}=0 to 10V	-	23	30	nC
Gate to drain charge	Q_{gd}		-	25	38	
Gate charge total	Q_g		-	136	177	
Gate plateau voltage	$V_{plateau}$		-	2.8	-	V
Reverse Diode						
Diode continous forward current[5]	I_S	T_C=25°C	-	-	257	A
Diode pulse current[5]	$I_{S,pulse}$		-	-	1748	
Diode forward voltage	V_{SD}	V_{GS}=0V, I_F=60A, T_j=25°C	-	0.8	1.1	V
Reverse recovery time[2]	t_{rr}	V_R=20V, I_F=50A, di_F/dt=100A/µs	-	71	-	ns
Reverse recovery charge[2]	Q_{rr}		-	98	-	nC

[1] Practically the current is limited by overall system design including customer specific PCB.

[2] The parameter is not subject to production test - verified by characterization.

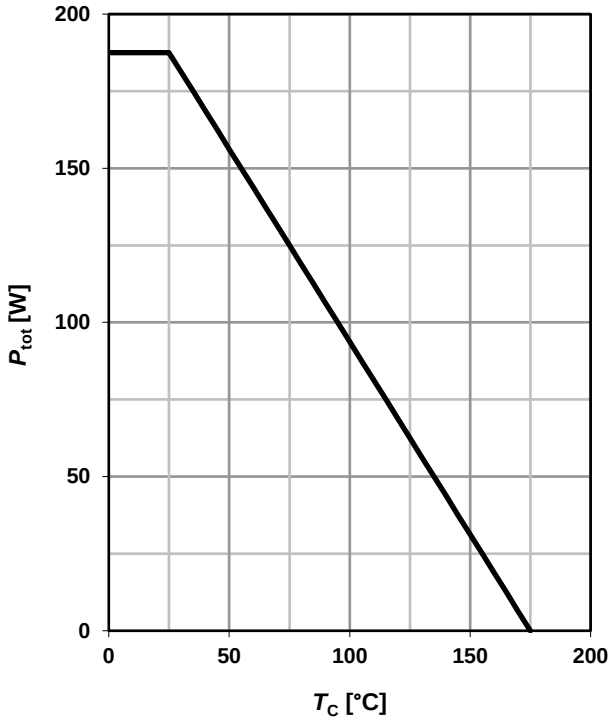
[3] The product can operate at specified current based on best practice to minimize electromigration at the solder joint. For rare events and inrush currents the value may be exceeded.

[4] Device on 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5, -7). PCB is vertical in still air.

[5] The parameter is not subject to production test - verified by design.

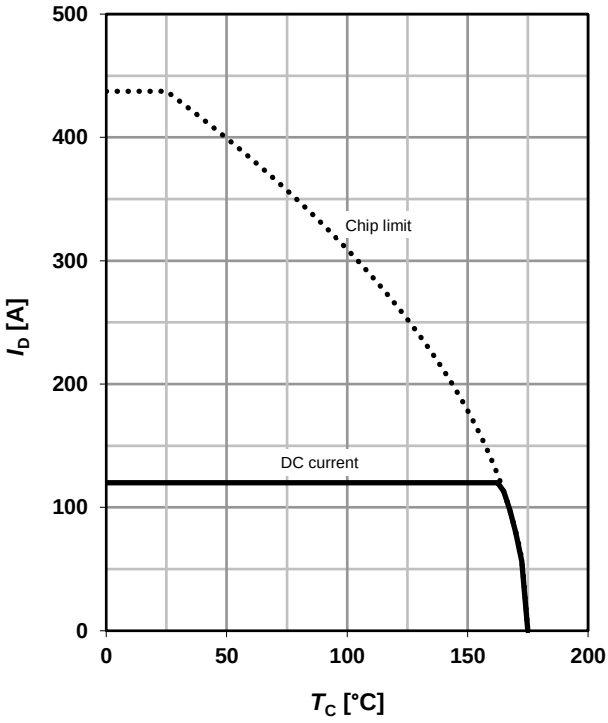
1 Power dissipation

$P_{tot} = f(T_C)$; $V_{GS} = 10$ V



2 Drain current

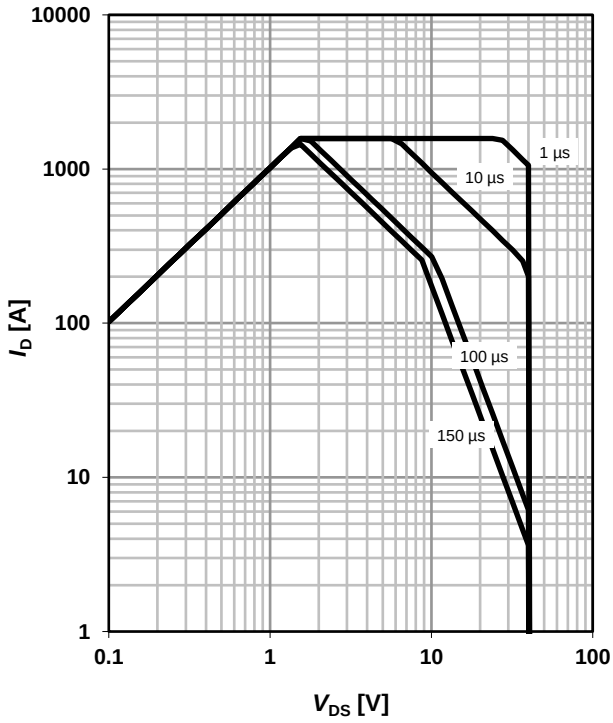
$I_D = f(T_C)$; $V_{GS} = 10$ V



3 Safe operating area

$I_D = f(V_{DS})$; $T_C = 25$ °C; $D = 0$

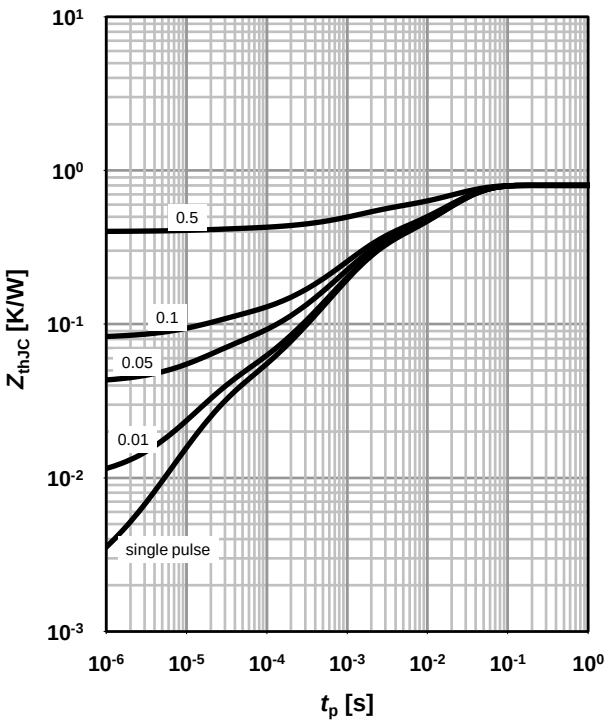
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$

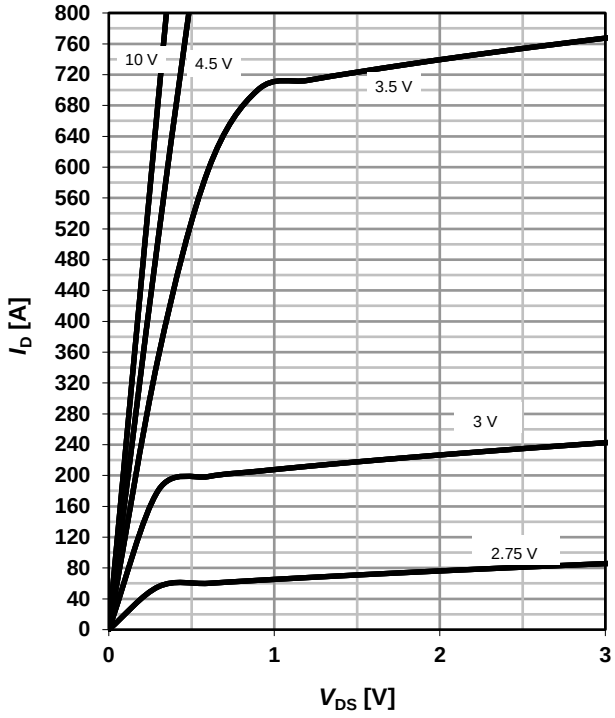
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS})$; $T_j = 25$ °C

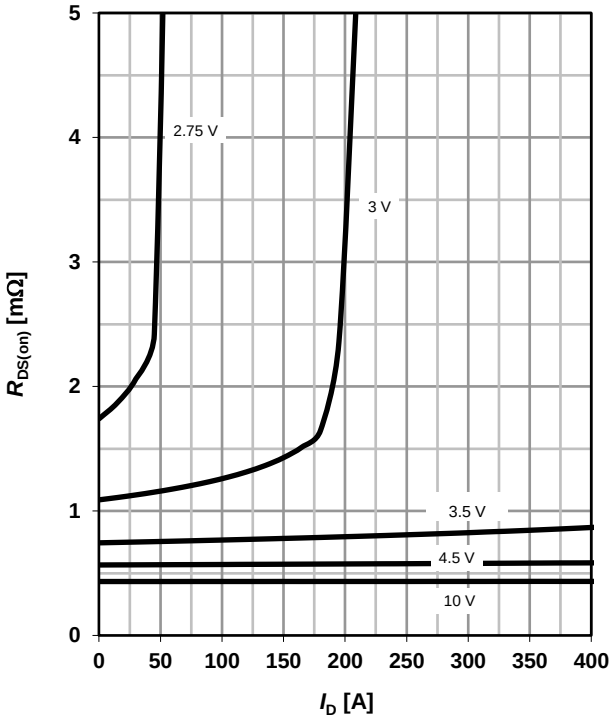
parameter: V_{GS}



6 Typ. drain-source on-state resistance

$R_{DS(on)} = f(I_D)$; $T_j = 25$ °C

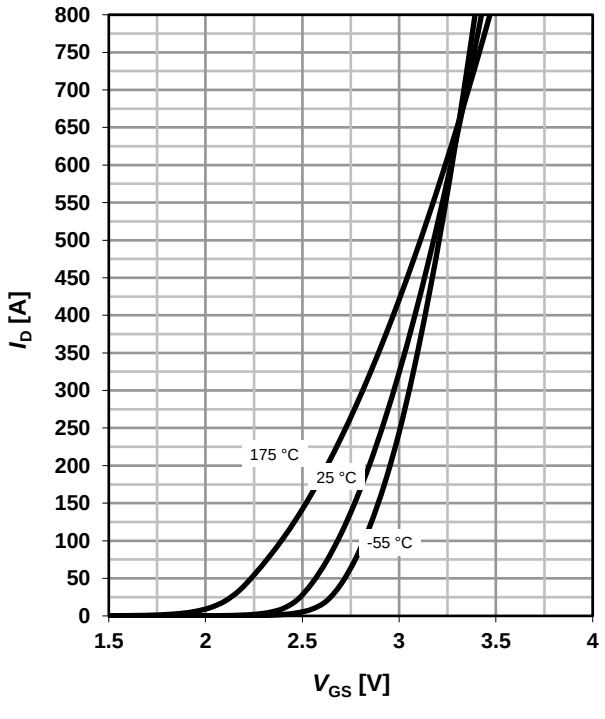
parameter: V_{GS}



7 Typ. transfer characteristics

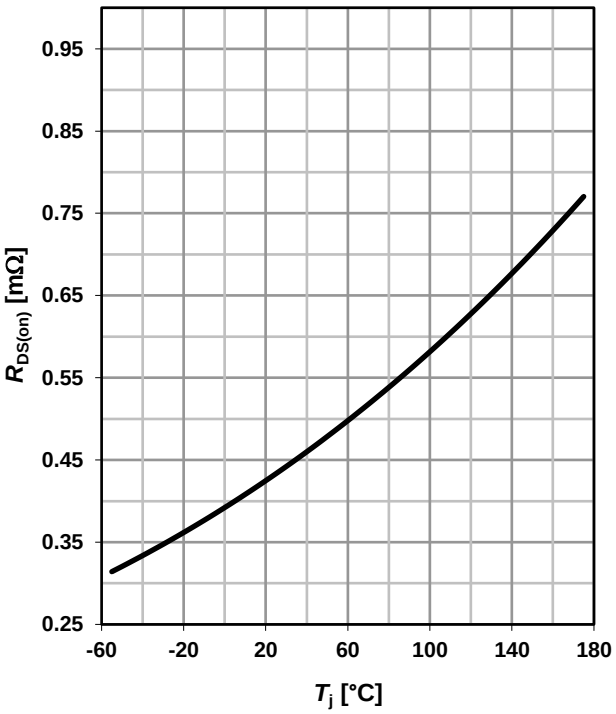
$I_D = f(V_{GS})$; $V_{DS} = 6$V

parameter: T_j



8 Typ. drain-source on-state resistance

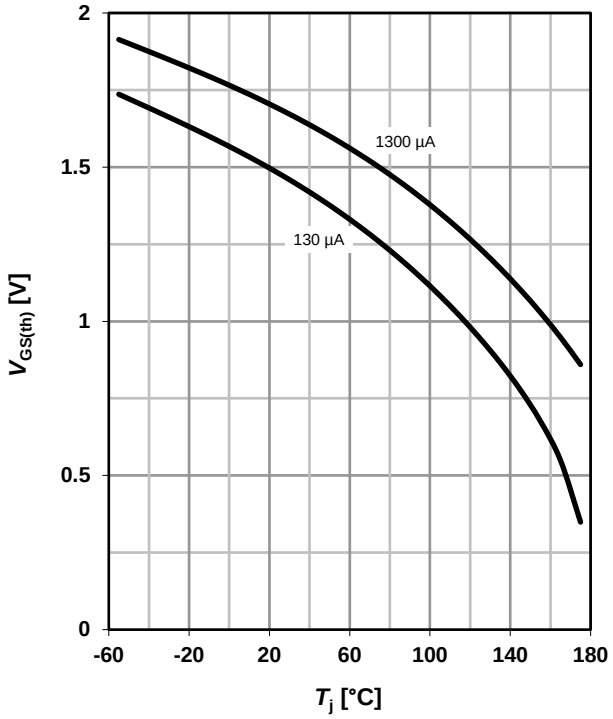
$R_{DS(on)} = f(T_j)$; $I_D = 60$ A; $V_{GS} = 10$ V



9 Typ. gate threshold voltage

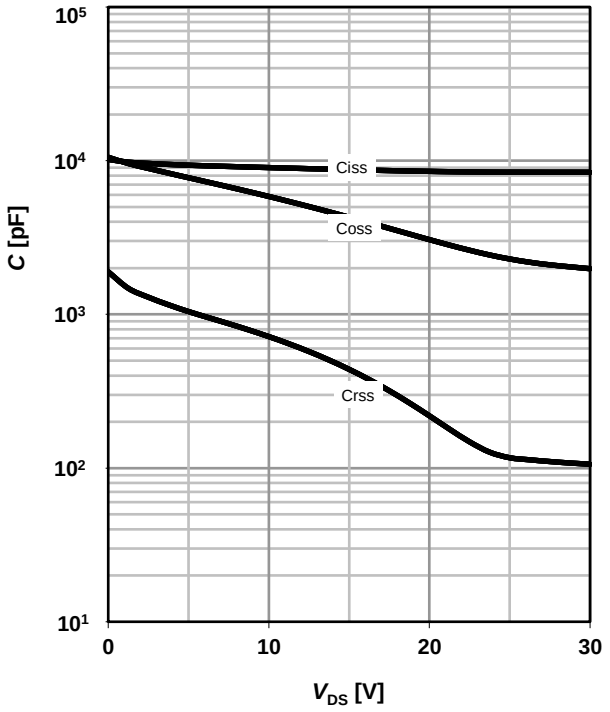
$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$

parameter: I_D



10 Typ. capacitances

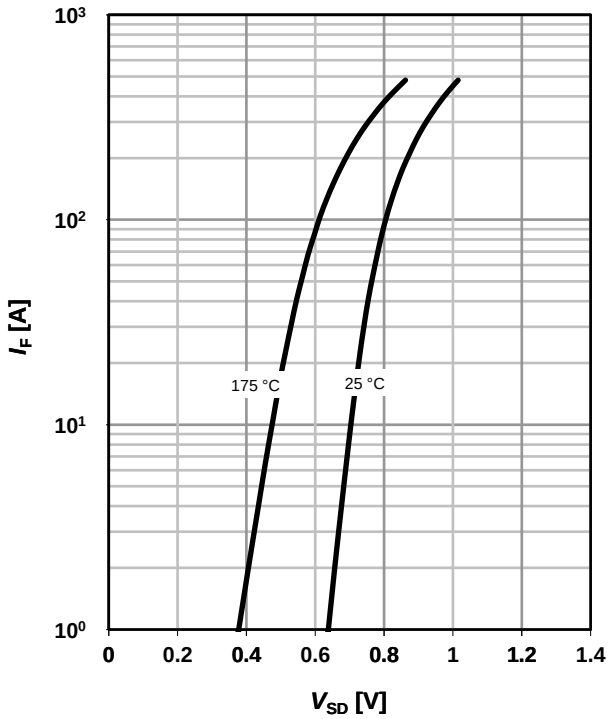
$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz



11 Typical forward diode characteristicis

IF = f(V_{SD})

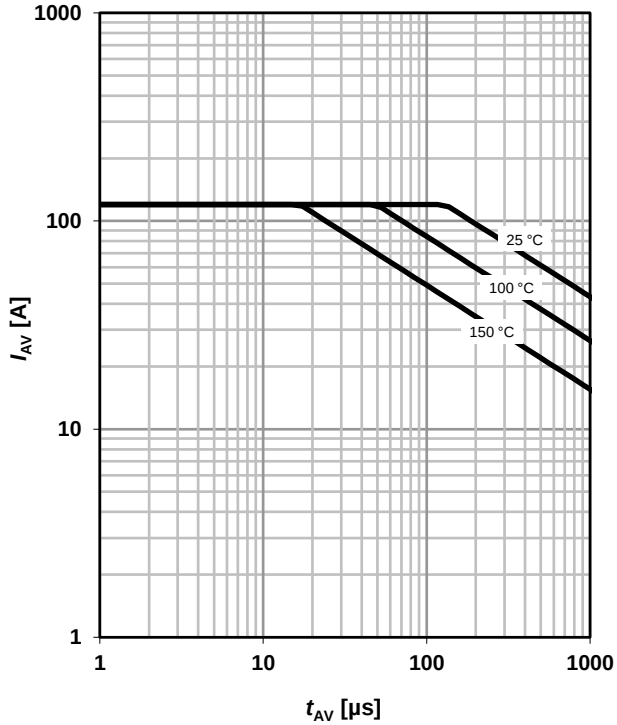
parameter: T_j



12 Avalanche characteristics

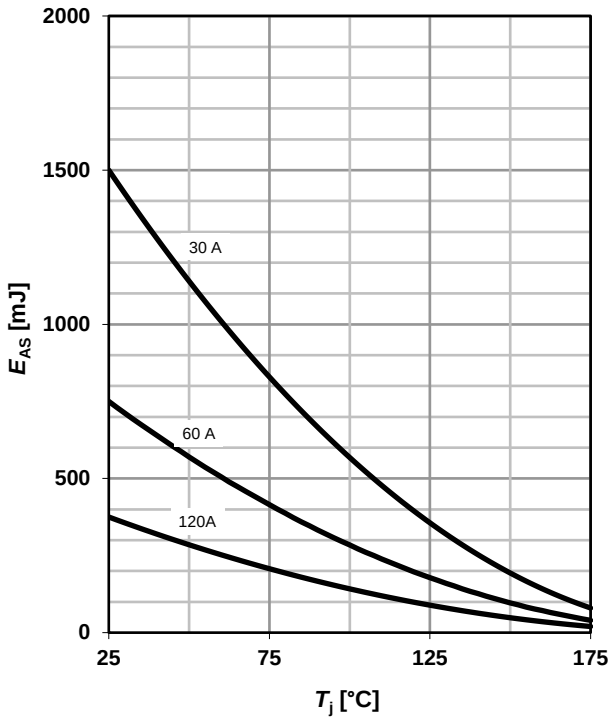
$I_{AS} = f(t_{AV})$

parameter: $T_{j(start)}$ >25°C



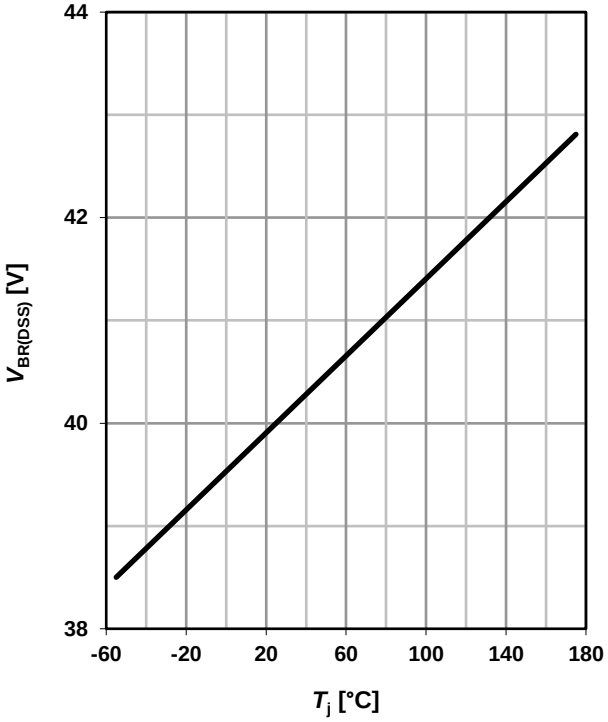
13 Avalanche energy

$E_{AS} = f(T_j)$



14 Drain-source breakdown voltage

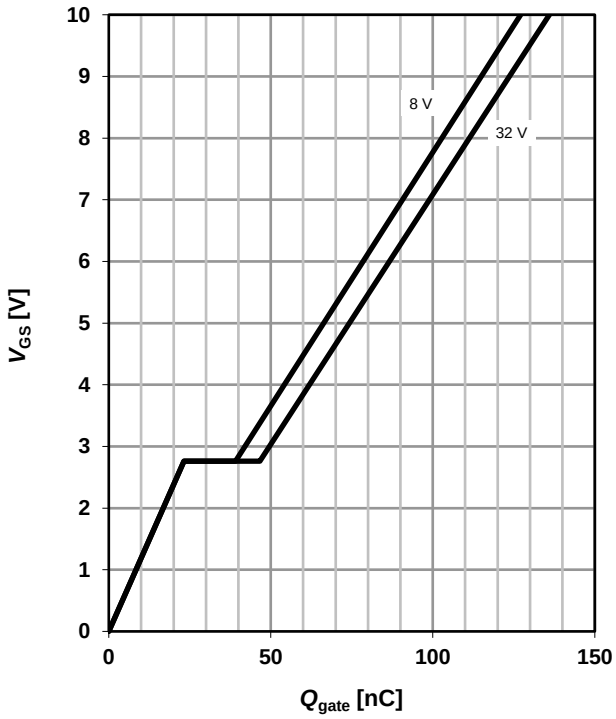
$V_{BR(DSS)} = f(T_j)$; I_D = 1 mA



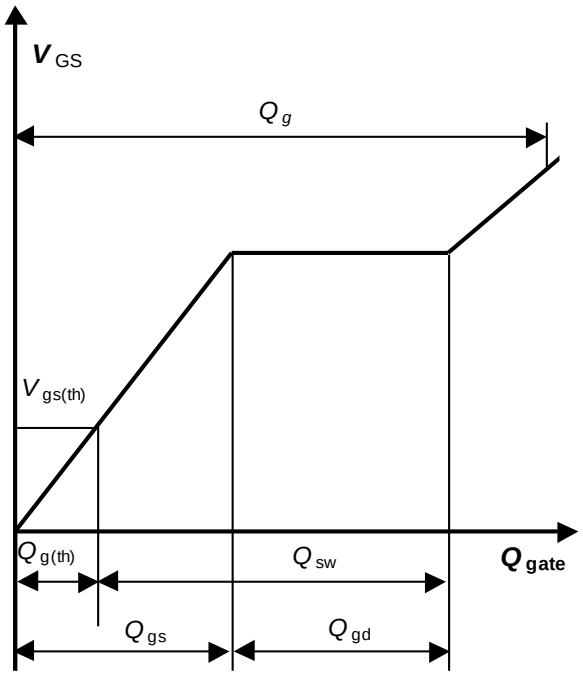
15 Typ. gate charge

$V_{GS} = f(Q_{gate})$; I_D = 120 A pulsed

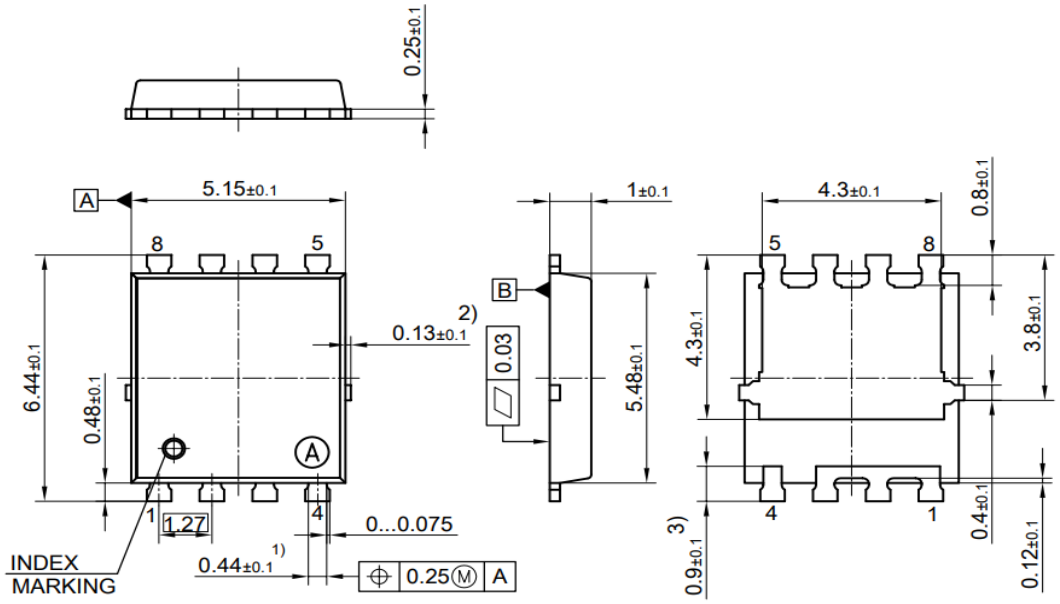
parameter: V_{DD}



16 Gate charge waveforms

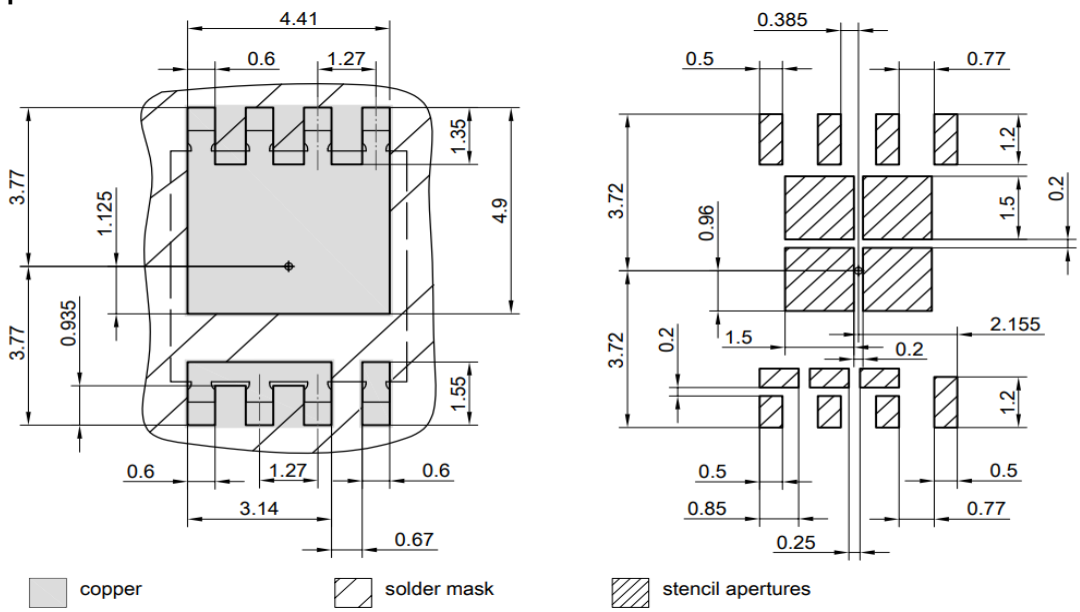


PG-TDSON-8: Outline



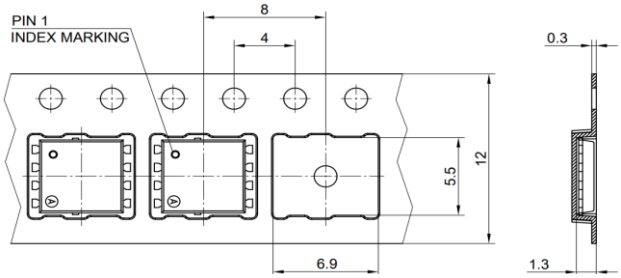
1) EXCLUDE MOLD FLASH
2) REMOVAL ON MOLD GATE, INTRUSION 0.1MM AND PROTRUSION 0.1MM
3) LEAD LENGTH UP TO ANTI FLASH LINE
4)ALL METAL SURFACE ARE PLATED, EXCEPT AREA OF CUT
ALL DIMENSIONS ARE IN UNITS MM
THE DRAWING IS IN COMPLIANCE WITH ISO 128 & PROJECTION METHOD 1 [ ]

Footprint



Dimensions in mm

Packaging



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If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Revision History

Version	Date	Changes
Revision 1.0	05.06.2020	Final Data Sheet